D882 TRANSISTOR（NPN）

TO-126 Plastic-Encapsulate Transistors

FEATURES

Power dissipation

P_{CM} : 1.25 W（Tamb=25℃）

Collector current

I_{CM} : 3 A

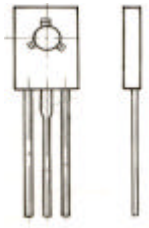
Collector-base voltage

$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

TO—126



1. EMITTER
2. COLLECTOR
3. BASE

1 2 3

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

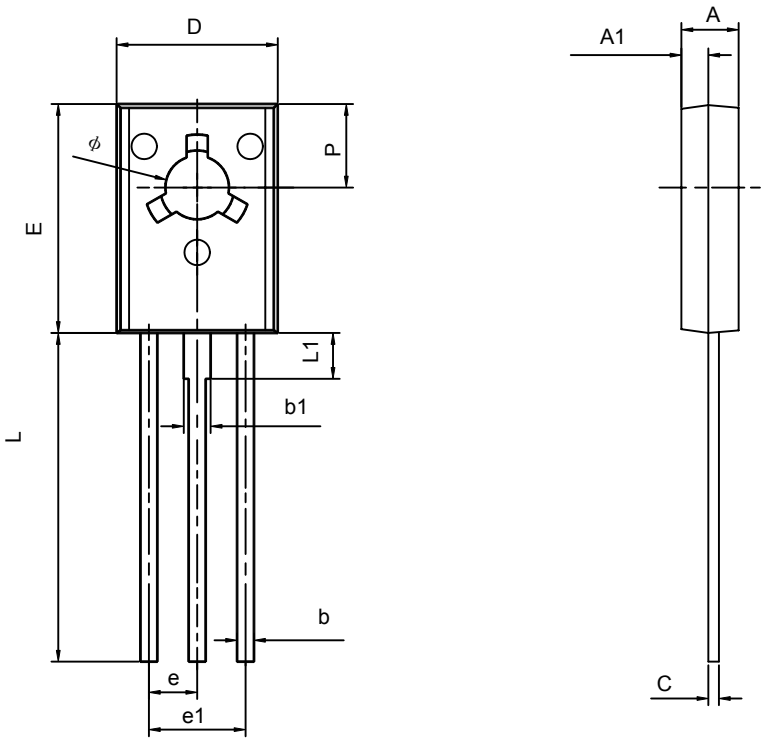
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic=100μA，I_E=0	40			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= 10 mA， I_B=0	30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100 μA，I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=40 V， I_E=0			1	μA
Collector cut-off current	I_{CEO}	V_{CE}=30 V， I_B=0			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=6V， I_C=0			1	μA
DC current gain	$h_{FE\ (1)}$	V_{CE}= 2V, I_C= 1A	60		400	
	$h_{FE\ (2)}$	V_{CE}=2V, I_C= 100mA	32			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=2A, I_B= 0.2A			0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=2A, I_B= 0.2A			1.5	V
Transition frequency	f_T	V_{CE}=5 V, Ic=0.1mA f = 10MHz	50			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

TO-126 Plastic-Encapsulate Transistors

TO-126 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.500	2.900	0.098	0.114
A1	1.100	1.500	0.043	0.059
b	0.660	0.860	0.026	0.034
b1	1.170	1.370	0.046	0.054
c	0.450	0.600	0.018	0.024
D	7.400	7.800	0.291	0.307
E	10.600	11.000	0.417	0.433
e	2.290TYP		0.090TYP	
e1	4.480	4.680	0.176	0.184
L	15.300	15.700	0.602	0.618
L1	2.100	2.300	0.083	0.091
P	3.900	4.100	0.154	0.161
ϕ	3.000	3.200	0.118	0.126